E. Compound Semiconductors 분과

2017년 2월 14일 (화), 10:10-11:40
Room D (크리스탈, 2층)

[TD2-E] WBG High Frequency Device

좌장: 민병규(한국전자통신연구원), 차호영(홍익대학교)

TD2-E-1 **10:10-10:25**	**Growth of 10 nm-thick AlIn(Ga)N/GaN Heterostructure with High Electron Mobility and Low Sheet Resistance** Seung-Hyeon Kang, Chul-Ho Won, Young-Woo Jo, Ryun-Hwi Kim, Jun-Hyeok Lee, Jeong-Gil Kim, Dai Quan, Chan Heo, Gokhan Atmaca, Dong Yan, and Jung-Hee Lee *School of Electrical Engineering, Kyungpook National University*
TD2-E-2 **10:25-10:40**	**Improvement of Thermal Reliability for GaN Microwave Device Using Molybdenum Insertion Gate Metal** Dong-Hwan Kim, Su-Keun Eom, Ho-Young Cha, and Kwang-Seok Seo *Department of Electrical and Computer Engineering, Seoul National University*
TD2-E-3 **10:40-10:55**	**Gate Capacitance Modeling in InGaAs Quantum-Well MOSFETs** Jung Ho Park, Do-Kywn Kim, Ji Min Baek, Seung-Woo Son, Jung-Hee Lee, and Dae-Hyun Kim *School of Electronics Engineering, Kyungpook National University*
TD2-E-4 **10:55-11:10**	**L_g = 0.5 μm $In_{0.7}Ga_{0.3}As$ PHEMTs with f_T = 126 GHz and f_{max} = 352 GHz** Ji Min Baek[1], Seung Woo Son[1], Jung Ho Park[1], Do-Kywn Kim[1], Jacoby Yoon[2], Jong-Keun Park[2], Jeong-Geun Kwak[2], Dong-Soo Bang[2], and Dae-Hyun Kim[1] *[1]School of Electronics Engineering, Kyungpook National University, [2]Quantum Semiconductor International (QSI) Co., Ltd.*
TD2-E-5 **11:10-11:25**	**Record Carrier Transport Properties in InGaAs Quantum-Well MOSFETs on 300-mm Si Substrate** Seung-Woo Son, Jung Ho Park, Ji Min Baek, Do-Kywn Kim, Jung-Hee Lee, and Dae-Hyun Kim *School of Electronics Engineering, Kyungpook National University*